

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

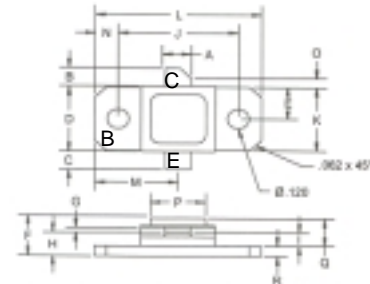
The **ASI PZ1418B30U** is Designed for Class B broadband Amplifiers under CW conditions, in 1.4 to 1.8 GHz Military Equipment.

FEATURES:

- Class B Operation
- $P_G = 7.3$ dB at 27 W/1.4-1.8 GHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	4.0 A
V_{CBO}	40 V
V_{CEO}	15 V
V_{EBO}	3.0 V
P_{DISS}	45 W @ $T_C = 25$ °C
T_J	+200 °C Max.
T_{STG}	-65 °C to +150 °C
θ_{JC}	4.0 °C/W

PACKAGE STYLE .400 4L FLG


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.140 / 3.50	
B	.110 / 2.80	
C	.110 / 2.80	
D	.360 / 9.03	.407 / 10.34
E	.190 / 4.80	
F		.230 / 5.84
G	.003 / 0.08	.008 / 0.15
H	.110 / 3.00	.121 / 3.03
I	.060 / 1.50	
J	.050 / 1.25	
K	.300 / 7.60	
L	.060 / 2.28	
M	.450 / 11.43	
N	.125 / 3.18	
Q	.050 / 1.27	
P	.400 / 10.20	
R	.170 / 4.32	
R	.062 / 1.58	

CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 1.0$ mA	40			V
BV_{CEO}	$I_C = 20$ mA	15			V
BV_{EBO}	$I_E = 0.25$ mA	3.0			V
I_{CBO}	$V_{CB} = 30$ V $V_{CB} = 40$ V			5.0 10	mA
I_{CES}	$V_{CE} = 35$ V			50	mA
I_{EBO}	$V_{EB} = 1.5$ V			200	μA
P_G	$V_{CC} = 28$ V $P_{OUT} = 27$ W $f = 400$ MHz	7.3	8.4		dB
η_D		38	45		%

